

Listing Of Claims

Claims 1-65 (Canceled)

66. (new) A contact for a semiconductor component having a component contact comprising:

a substrate; and

an electrically conductive silicon carbide layer on the substrate configured to electrically engage the component contact.

67. (new) The contact of claim 66 further comprising a conductive via in the substrate in electrical communication with the silicon carbide layer.

68. (new) The contact of claim 66 further comprising a silicon carbide conductor on the substrate in electrical communication with the silicon carbide layer.

69. (new) The contact of claim 66 wherein the silicon carbide layer comprises oxidized silicon carbide.

70. (new) The contact of claim 66 wherein the silicon carbide layer comprises doped silicon carbide.

71. (new) The contact of claim 66 wherein the silicon carbide layer at least partially covers a projection on the substrate.

72. (new) The contact of claim 71 wherein the silicon carbide layer substantially surrounds the projection.

73. (new) The contact of claim 66 wherein the silicon carbide layer at least partially covers an indentation in the substrate.

74. (new) The contact of claim 73 wherein the silicon carbide layer substantially surrounds the indentation.

75. (new) The contact of claim 66 wherein the substrate comprises a die level interconnect configured to electrically engage a semiconductor die or a semiconductor package.

76. (new) The contact of claim 66 wherein the substrate comprises a wafer level interconnect configured to electrically engage a semiconductor wafer.

77. (new) A contact for a semiconductor component having a component contact comprising:

a substrate;

a projection on the substrate; and

an electrically conductive silicon carbide layer on the projection configured to electrically engage the component contact.

78. (new) The contact of claim 77 further comprising a conductive via in the substrate in electrical communication with the silicon carbide layer.

79. (new) The contact of claim 77 further comprising a silicon carbide conductor on the substrate in electrical communication with the silicon carbide layer.

80. (new) The contact of claim 77 wherein the projection is configured to penetrate the component contact.

81. (new) The contact of claim 77 wherein the component contact comprises a pad and the projection is configured to penetrate the pad.

82. (new) The contact of claim 77 wherein the component contact comprises a bump and the projection is configured to penetrate the bump.

83. (new) The contact of claim 77 wherein the silicon carbide layer comprises oxidized silicon carbide.

84. (new) The contact of claim 77 wherein the silicon carbide layer comprises doped silicon carbide.

85. (new) The contact of claim 77 wherein the silicon carbide layer substantially surrounds the projection.

86. (new) The contact of claim 77 wherein the substrate comprises silicon.

87. (new) The contact of claim 77 wherein the component comprises a semiconductor die or a semiconductor package.

88. (new) The contact of claim 77 wherein the component comprises a semiconductor wafer.

89. (new) A contact for a semiconductor component having a component contact comprising:

a substrate;

an indentation in the substrate; and

an electrically conductive silicon carbide layer on the indentation configured to electrically engage the component contact.

90. (new) The contact of claim 89 further comprising a conductive via in the substrate in electrical communication with the silicon carbide layer.

91. (new) The contact of claim 89 further comprising a silicon carbide conductor on the substrate in electrical communication with the silicon carbide layer.

92. (new) The contact of claim 89 wherein the component contact comprises a bump and the indentation is configured to retain the bump.

93. (new) The contact of claim 89 wherein the silicon carbide layer comprises oxidized silicon carbide.

94. (new) The contact of claim 89 wherein the silicon carbide layer comprises doped silicon carbide.

95. (new) The contact of claim 89 wherein the silicon carbide layer substantially surrounds the indentation.

96. (new) The contact of claim 89 wherein the substrate comprises silicon.

97. (new) The contact of claim 89 wherein the component comprises a semiconductor die or a semiconductor package.

98. (new) The contact of claim 89 wherein the component comprises a semiconductor wafer.

99. (new) A contact for a semiconductor component having a plurality of component contacts comprising:

a substrate;

a plurality of projections on the substrate configured to electrically engage the component contacts; and

a plurality of electrically conductive silicon carbide layers on the projections substantially covering the substrate.

100. (new) The contact of claim 99 wherein the silicon carbide layers comprise oxidized silicon carbide or doped silicon carbide.

101. (new) The contact of claim 99 wherein the silicon carbide layers include a plurality of conductors.